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<p>MUTAXASSISLIGI</p>	<ul style="list-style-type: none"> • Yarimo‘tkazgichlar fizikasi
<p>O‘QITADIGAN FANLARI</p>	<ul style="list-style-type: none"> • Yarimo‘tkazgich asboblarni modellashtirish, Yarimo‘tkazgichli elektronika asoslari, Yarimo‘tkazgich va dielektiklar fizikasi
<p>TADQIQOT ISHI</p>	<ul style="list-style-type: none"> • Nanolchamli yarimotkazgich asboblarni modellashtirish.
<p>TADQIQOTLARI</p>	<ul style="list-style-type: none"> • 2017-2020. “Si-SiO₂ chegara va oksid katlamida nuksonlarni taksimotini aniklashga yangicha yondashish”. Loyixa. Innovacion rivojlanish vazirligi. • 2021-2023. Xindiston –Ozbekiston koshma loyixasi “Self Heating Effect on stacked Nanosheet Field Effect Transistor”
<p>HOZIRGI TADQIQOTLARI</p>	<ol style="list-style-type: none"> 1. A.E. Atamuratov, R. Granzner , M. Kittler, Z. Atamuratova, M. Halillaev, F. Schwierz . Simulation of Random Telegraph Noise in nanometer nMOSFET induced by interface and oxide trapped charge. NATO Advanced Research Workshop on Low Dimensional Functional Materials, October 15-19, 2012, Tashkent 2. A.E. Atamuratov , Z. Atamuratova, M. Halillaev, G. Ghione. Simulation of carrier distribution in nanometer MNOSFET with single charge trapped in oxide and at SiO₂ – Si₃N₄ interface. Materials of International conference Low dimensional nanoscale systems: quantum effects, particle transport and advanced materials. November 6-7,2012, Tashkent. 3. Matyakubov H., Atamuratova Z. A., Abdikarimov A., Halillaev M., Atamuratov A.E. The method of estimation of single trapped charge position in nanometer MNOSFET oxide layer and Si-SiO₂ interface. Materials of International conference Fundamental and Applied Problems of Physics November 14-16,2013, Tashkent. 4. A.E.Atamuratov, U.A.Aminov, Z.A. Atamuratova, M. Halillaev, A. Abdikarimov ,

- H. Matyakubov. The lateral capacitance of nanometer MNOSFET with a single charge trapped in oxide layer or at SiO₂ - Si₃N₄ interface. *Nanosystems: physics, chemistry, mathematics*, 2015, 6 (6), p. 837–842
5. A. E. Atamuratov, A. Abdikarimov, M. Khalilloev, Z. A. Atamuratova, R. Rahmanov, A. Garcia-Loureiro, A. Yusupov, Simulation study of diban effect in 25 nm soi-finfet with the different body shape, *Nanosystems: Physics, Chemistry, Mathematics*, 2017. 8 (1), p. 71–74
6. A. E. Atamuratov, M. Khalilloev, A. Abdikarimov, Z. A. Atamuratova, M. Kittler, R. Granzner, F. Schwierz, Influence of non-uniform lateral interface defects distribution to the current-voltage characteristic of MOSFET. *Nanosystems: physics, chemistry, mathematics*, 2017, 8 (1), p. 75–78.
7. Atamuratov A. E., Abdikarimov A., Atamuratova Z. A., Xolillaev M., Yusupov A. Collection of papers (Urgench state university). Actual problems of modern science, education and training in the region 8-12 page, N1, 2017
8. A. E. Atamuratov, Z. A. Atamuratova, A. Yusupov, A. Ghani., Characterising lateral capacitance of MNOSFET with localised trapped charge in nitride layer. *Results in Physics*, V.11, 2018, pp. 656–658..
9. Z. A. Atamuratova, A. Yusupov, B. O. Khalikberdiev, and A. E. Atamuratov Anomalous Behavior of Lateral C–V Characteristic of an MNOS Transistor with an Embedded Local Charge in the Nitride Layer. *Technical Physics*, 2019, Vol. 64, No. 7, pp. 1006–1009.
10. Atabek E. Atamuratov, Ahmed Yusupov, Zukhra A. Atamuratova, Jean Chamberlain Chedjou and Kyamakya Kyandoghere. Lateral Capacitance–Voltage Method of NanoMOSFET for Detecting the Hot Carrier Injection. *Appl. Sci.* 2020, 10(21), 7935; doi:10.3390/app10217935